

Amendment dated

Reply to Office Action of November 15, 2007

**REMARKS**

Applicants affirm the election of Group I, method claims 1-9, for prosecution. These claims are all drawn to a method of manufacturing a crystallized semiconductor device. Group II, claim 10, and Group III, claims 11-15, are withdrawn. The restriction requirement is not traversed.

Claim 1 is amended so that the thermal diffusion layer is defined as being formed "on the semiconductor layer." The phrase "a surface of " is simply deleted. Because the thermal diffusion layer is defined as being formed on a substrate, the amended claim clearly defines the multi-layer structure shown in Figs. 1 and 8 and described in the specification. The objection to claim 1 is therefore believed to be moot and overcome.

Claim 1 is also amended to further specify that the irradiation of the semiconductor layer with laser light is formed into a slit image on the semiconductor layer. This limitation is supported by the disclosure in the specification at least at page 25, line 3 to page 26, line 3.

Applicants respectfully traverse the rejection of claims 1-4 and 7-9 under 35 USC 102(b) as anticipated by Okumura Nobu Japanese Publication No. 09-092839.

All of the pending claims now include the limitation that the laser light is "formed into a slit image on the semiconductor." This feature, in combination with the other claim elements, produces the advantages detailed on page 31, line 7 to page 34, line 21 of the specification. Using the claimed method it is possible to grow crystals of growth length L that are two to three times the length of crystals in the conventional case, as compared to conventional arrangements discussed in the Background of the Invention, and whose crystal growth is illustrated in Figs. 4 and 5. The combination of the stacked substrate-semiconductor layer-thermal diffusion layer with laser light irradiation from above the thermal diffusion layer in a slit formed on the semiconductor layer facilitates a lateral flow of heat in the semiconductor layer. As shown in Fig. 7, and as stated at page 33, lines 11-14:

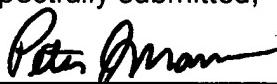
... the crystal grows smoothly from the outer edge portion [adjacent the edges of the slit irradiation] towards the central portion. As a result, it is possible to generate a longer crystal than before from the outer edge portion to the central portion.

Applicants urge that the Okumura Nobu reference does not teach this combination and these results.

In view of the foregoing amendments, Remarks and election, Applicants believe the pending application is in condition for allowance.

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Respectfully submitted,

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